Power MOSFET, 57 A

SOT-227

FEATURES

- Fully isolated package
- Easy to use and parallel
- Low on-resistance
- Dynamic dV/dt rating
- Fully avalanche rated
- Simple drive requirements
- Low gate charge device
- Low drain to case capacitance
- Low internal inductance
- UL pending
- Compliant to RoHS directive 2002/95/EC
- Designed for industrial level

Pb-free
RoHS COMPLIANT

DESCRIPTION

Third Generation Power MOSFETs from Vishay HPP provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-227 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 500 W. The low thermal resistance of the SOT-227 contribute to its wide acceptance throughout the industry.

PRODUCT SUMMARY	
V_{DSS}	500 V
$R_{DS(on)}$	0.08 Ω
I_D	57 A
Type	Modules - MOSFET
Package	SOT-227

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Continuous drain current at V_{GS} 10 V	I_D	T_C = 25 °C	57	A
		T_C = 100 °C	36	
Pulsed drain current	I_{DM} (1)		228	
Power dissipation	P_D	T_C = 25 °C	625	W
Linear derating factor			5.0	W/°C
Gate to source voltage	V_{GS}		± 20	V
Single pulse avalanche energy	E_{AS} (2)		725	mJ
Avalanche current	I_{AR} (1)		57	A
Repetitive avalanche energy	E_{AR} (1)		62.5	mJ
Peak diode recovery dV/dt	dV/dt (3)		10	V/ns
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C
Insulation withstand voltage (AC-RMS)	V_{ISO}		2.5	kV
Mounting torque		M4 screw	1.3	Nm

Notes

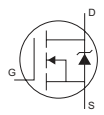
(1) Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
(2) Starting T_J = 25 °C, L = 446 µH, R_g = 25 Ω, I_{AS} = 57 A (see fig. 12)
(3) I_{SD} ≤ 57 A, dI/dt ≤ 200 A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150 °C

THERMAL RESISTANCE				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNITS**
Junction to case	R_{thJC}	-	0.20	°C/W
Case to sink, flat, greased surface	R_{thCS}	0.05	-	

ELECTRICAL CHARACTERISTCS (T_J = 25 °C unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Drain to source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1.0 mA	500	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	Reference to 25 °C, I_D = 1 mA	-	0.62	-	V/°C
Static drain to source on-resistance	$R_{DS(on)}$ (1)	V_{GS} = 10 V, I_D = 34 A	-	-	0.08	Ω
Gate threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	2.0	-	4.0	V
Forward transconductance	g_{fs}	V_{DS} = 50 V, I_D = 34 A	43	-	-	S
Drain to source leakage current	I_{DSS}	V_{DS} = 500 V, V_{GS} = 0 V	-	-	50	µA
		V_{DS} = 400 V, V_{GS} = 0 V, T_J = 125 °C	-	-	500	
Gate to source forward leakage	I_{GSS}	V_{GS} = 20 V	-	-	200	nA
Gate to source reverse leakage		V_{GS} = - 20 V	-	-	- 200	
Total gate charge	Q_g	I_D = 57 A V_{DS} = 400 V V_{GS} = 10 V; see fig. 6 and 13 (1)	-	225	338	nC
Gate to source charge	Q_{gs}		-	51	77	
Gate to drain ("Miller") charge	Q_{gd}		-	98	147	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 250 V I_D = 57 A R_g = 2.0 Ω (internal) R_D = 4.3 Ω, see fig. 10 (1)	-	32	-	ns
Rise time	t_r		-	152	-	
Turn-off delay time	$t_{d(off)}$		-	108	-	
Fall time	t_f		-	118	-	
Internal source inductance	L_S	Between lead, and center of die contact	-	5.0	-	nH
Input capacitance	C_{iss}	V_{GS} = 0 V V_{DS} = 25 V f = 1.0 MHz, see fig. 5	-	10 000	-	pF
Output capacitance	C_{oss}		-	1500	-	
Reverse transfer capacitance	C_{rss}		-	50	-	

Note

(1) Pulse width ≤ 300 µs, duty cycle ≤ 2 %

SOURCE-DRAIN RATINGS AND CHARACTERISTICS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Continuous source current (body diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 	-	-	57	A
Pulsed source current (body diode)	I_{SM} (1)		-	-	228	
Diode forward voltage	V_{SD} (2)	T_J = 25 °C, I_S = 57 A, V_{GS} = 0 V	-	-	1.3	V
Reverse recovery time	t_{rr}	T_J = 25 °C, I_F = 57 A, dI/dt = 100 A/µs (2)	-	901	1351	ns
Reverse recovery charge	Q_{rr}		-	15	23	µC
Forward turn-on time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S + L_D)				

Notes

(1) Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

(2) Pulse width ≤ 300 µs, duty cycle ≤ 2 %

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Revision: 12-May-10

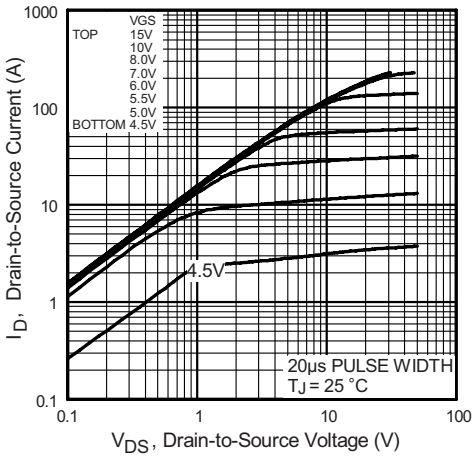

Fig. 1 - Typical Output Characteristics

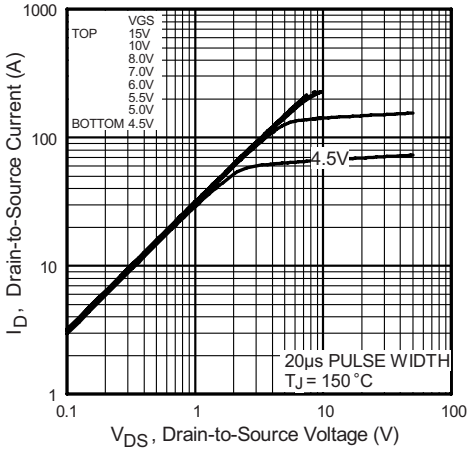

Fig. 2 - Typical Output Characteristics

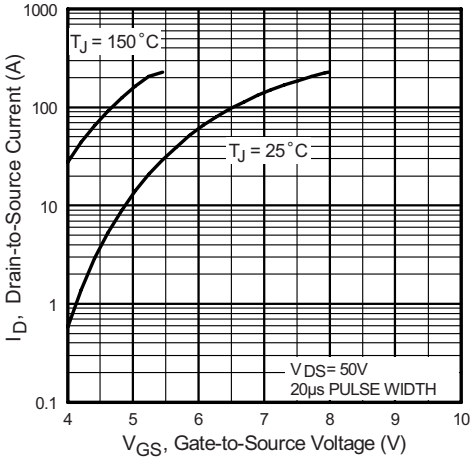

Fig. 3 - Typical Transfer Characteristics

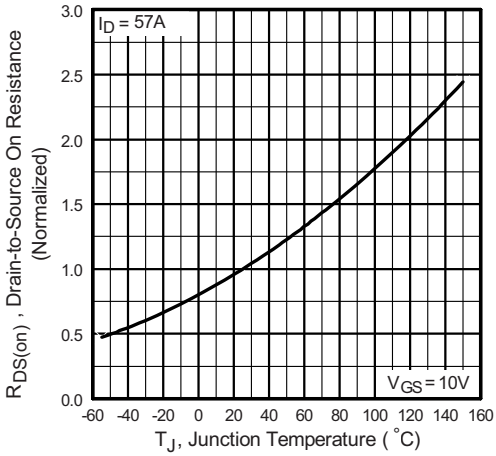

Fig. 4 - Normalized On-Resistance vs. Temperature

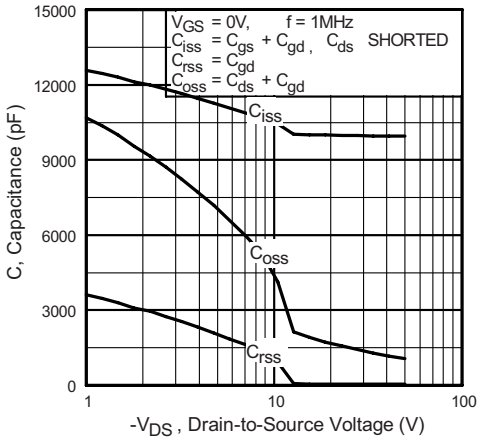

Fig. 5 - Typical Capacitance vs. Drain to Source Voltage

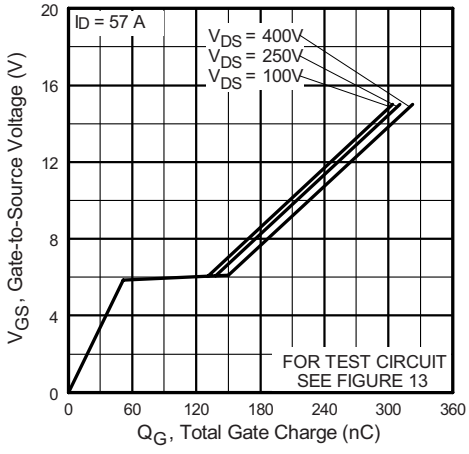

Fig. 6 - Typical Gate Charge vs. Gate to Source Voltage

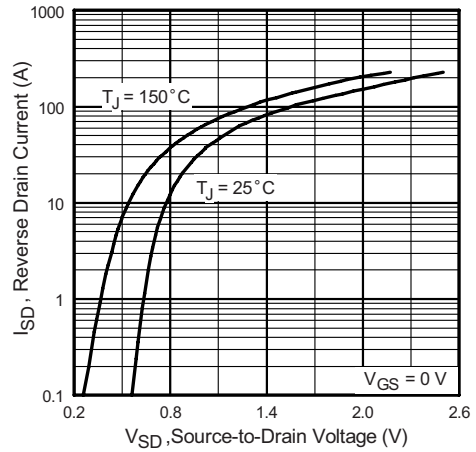

Fig. 7 - Typical Source Drain Diode Forward Voltage

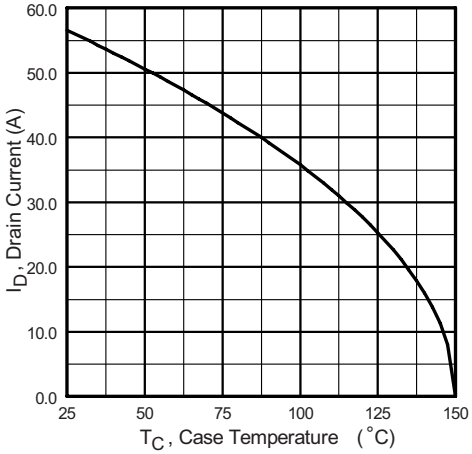

Fig. 9 - Maximum Drain Current vs. Case Temperature

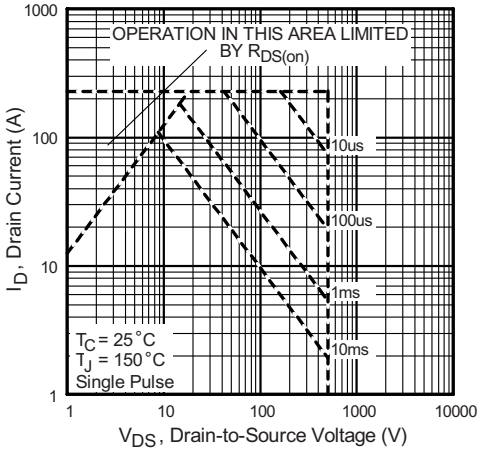

Fig. 8 - Maximum Safe Operating Area

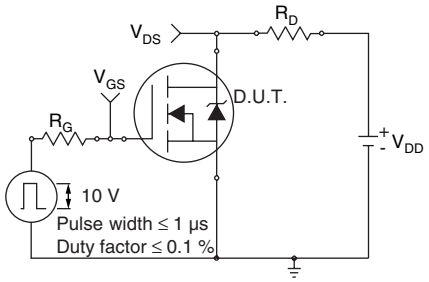

Fig. 10a - Switching Time Test Circuit

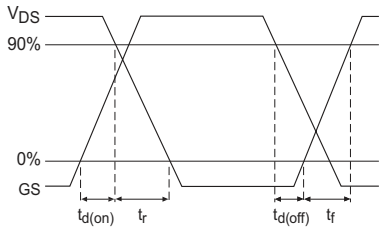

Fig. 10b - Switching Time Waveforms

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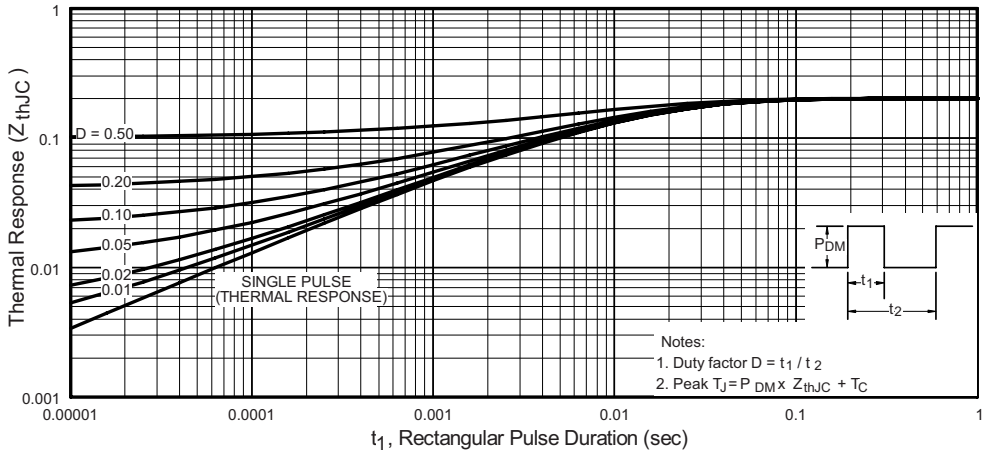


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction to Case

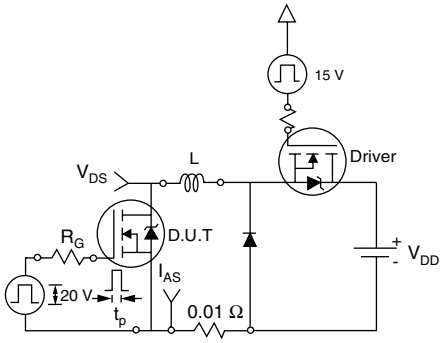


Fig. 12a - Unclamped Inductive Test Circuit

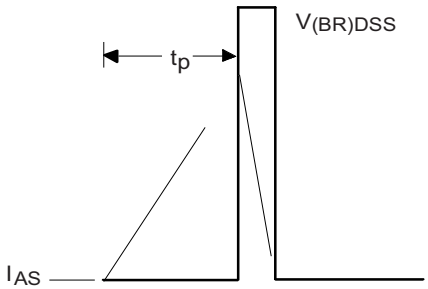


Fig. 12b - Unclamped Inductive Waveforms

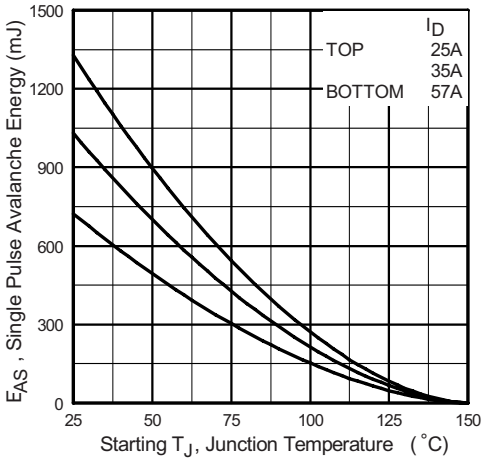


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

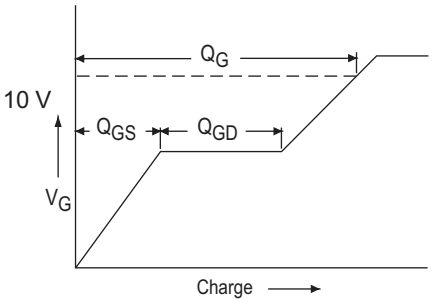


Fig. 13a - Basic Gate Charge Waveform

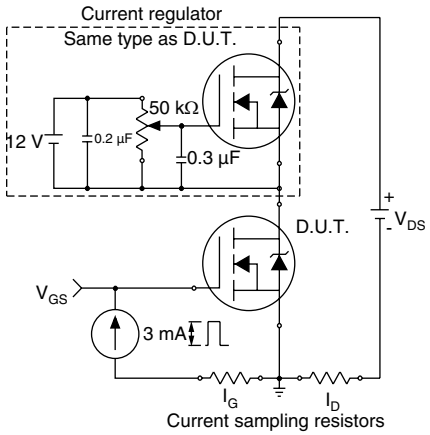


Fig. 13b - Gate Charge Test Circuit

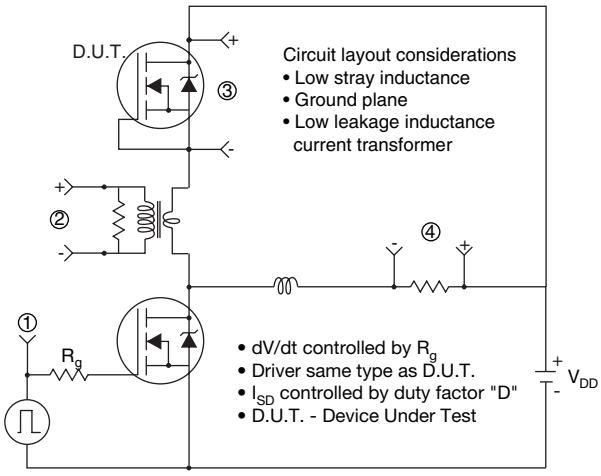
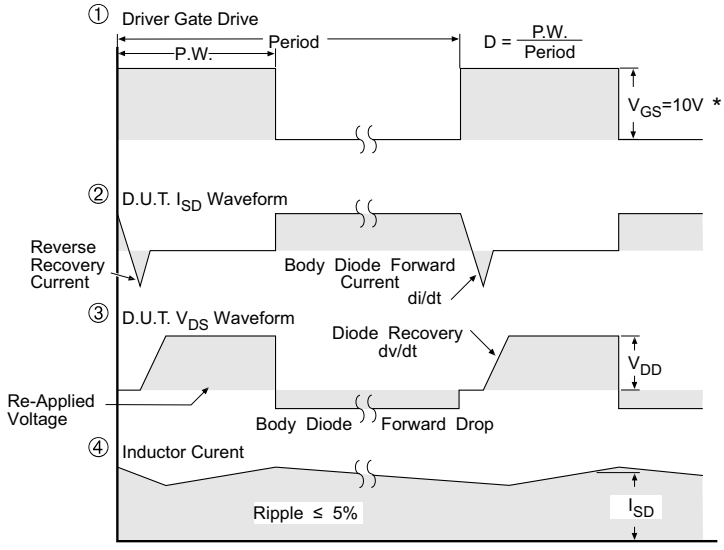


Fig. 13c - Peak Diode Recovery dV/dt Test Circuit



* V_{GS} = 5V for Logic Level Devices

Fig. 14 - For N-Channel Power MOSFETs

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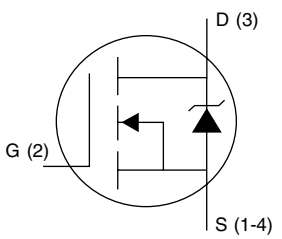
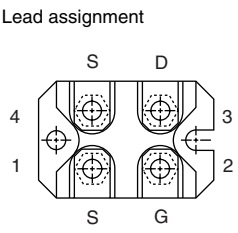
ORDERING INFORMATION TABLE

Device code

F	A	57	S	A	50	LC	P
1	2	3	4	5	6	7	8

1 - Power MOSFET
2 - Generation 3, MOSFET silicon, DBC construction
3 - Current rating (57 = 57 A)
4 - Single switch (see Circuit Configuration table)
5 - SOT-227
6 - Voltage rating (50 = 500 V)
7 - Low charge
8 - P = Lead (Pb)-free

CIRCUIT CONFIGURATION		
CIRCUIT	**CIRCUIT CONFIGURATION CODE**	**CIRCUIT DRAWING**
Single switch no diode	S	 

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95036
Packaging information	www.vishay.com/doc?95037

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